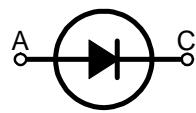
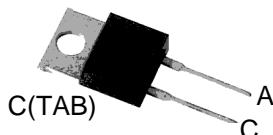


# MBR580 thru MBR5100

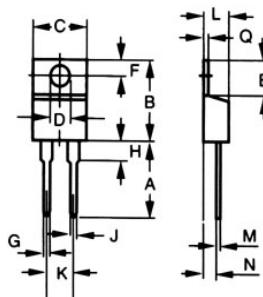
## Wide Temperature Range and High $T_{j\text{m}}$ Schottky Barrier Rectifiers



A=Anode, C=Cathode, TAB=Cathode

	$V_{RRM}$ V	$V_{RMS}$ V	$V_{DC}$ V
<b>MBR580</b>	80	56	80
<b>MBR5100</b>	100	70	100

Dimensions TO-220AC



Dim.	Inches Min.	Inches Max.	Milimeter Min.	Milimeter Max.
A	0.500	0.580	12.70	14.73
B	0.560	0.650	14.23	16.51
C	0.380	0.420	9.66	10.66
D	0.139	0.161	3.54	4.08
E	2.300	0.420	5.85	6.85
F	0.100	0.135	2.54	3.42
G	0.045	0.070	1.15	1.77
H	-	0.250	-	6.35
J	0.025	0.035	0.64	0.89
K	0.190	0.210	4.83	5.33
L	0.140	0.190	3.56	4.82
M	0.015	0.022	0.38	0.56
N	0.080	0.115	2.04	2.49
Q	0.025	0.055	0.64	1.39

Symbol	Characteristics	Maximum Ratings	Unit
$I_{(AV)}$	Maximum Average Forward Rectified Current @ $T_c=125^\circ\text{C}$	5	A
$I_{FSM}$	Peak Forward Surge Current 8.3ms Single Half-Sine-Wave Superimposed On Rated Load (JEDEC METHOD)	120	A
$dv/dt$	Voltage Rate Of Change (Rated $V_R$ )	10000	V/us
$V_F$	Maximum Forward Voltage (Note 1) $I_F=5\text{A} @ T_J=25^\circ\text{C}$ $I_F=5\text{A} @ T_J=125^\circ\text{C}$	0.85 0.75	V
$I_R$	Maximum DC Reverse Current @ $T_J=25^\circ\text{C}$ At Rated DC Blocking Voltage @ $T_J=125^\circ\text{C}$	0.05 10	mA
$R_{eJC}$	Typical Thermal Resistance (Note 2)	-	°C/W
$C_J$	Typical Junction Capacitance (Note 3)	400	pF
$T_J$	Operating Temperature Range	-50 to +150	°C
$T_{STG}$	Storage Temperature Range	-50 to +150	°C

NOTES: 1. 300us Pulse Width, Duty Cycle 2%.

2. Thermal Resistance Junction To Case.

3. Measured At 1.0MHz And Applied Reverse Voltage Of 4.0V DC.

### FEATURES

- \* Metal of silicon rectifier, majority carrier conductor
- \* Guard ring for transient protection
- \* Low power loss, high efficiency
- \* High current capability, low  $V_F$
- \* High surge capacity
- \* For use in low voltage, high frequency inverters, free whelling, and polarity protection applications

### MECHANICAL DATA

- \* Case: TO-220AC molded plastic
- \* Polarity: As marked on the body
- \* Weight: 0.08 ounces, 2.24 grams
- \* Mounting position: Any

**S**ilicon **r**ectifier®

# MBR580 thru MBR5100

## Wide Temperature Range and High $T_{j\text{m}}$ Schottky Barrier Rectifiers

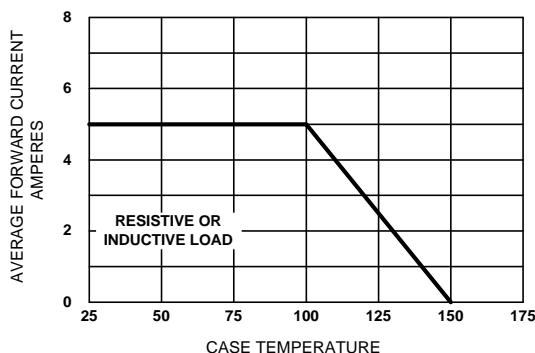


Figure 1. Forward Current Derating Curve

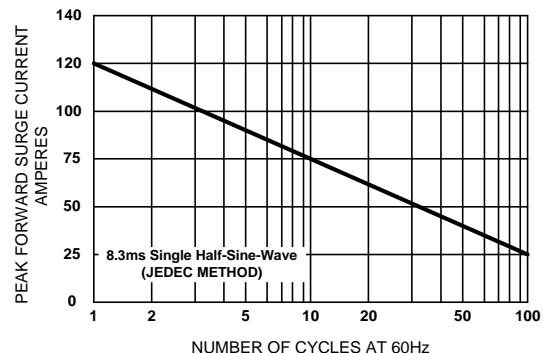


Figure 2. Maximum Non-repetitive Surge Current

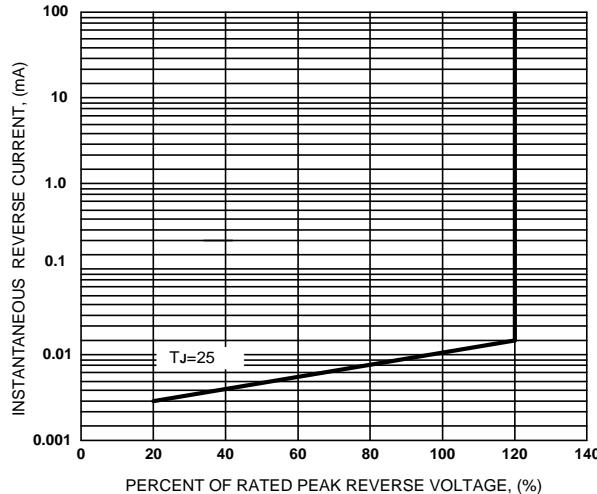


Figure 3. Typical Reverse Characteristics

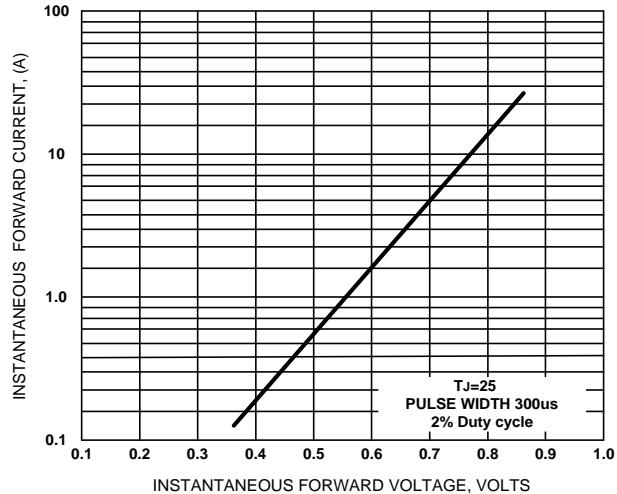


Figure 4. Typical Forward Characteristics

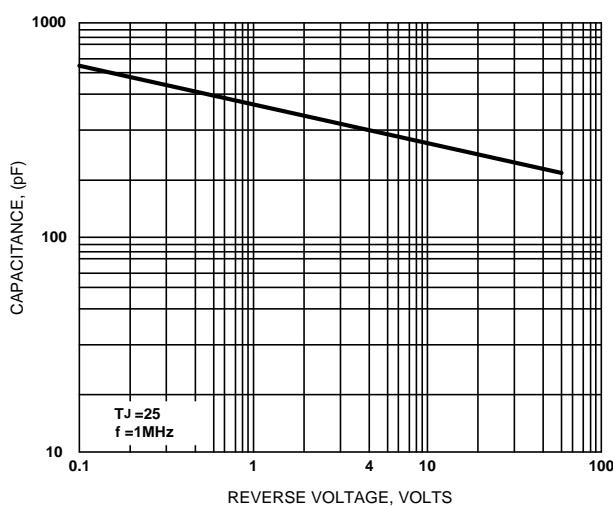


Figure 5. Typical Junction Capacitance